74HC7541; 74HCT7541

Octal Schmitt trigger buffer/line driver; 3-state Rev. 3 — 25 July 2011

Product data sheet

1. **General description**

The 74HC7541; 74HCT7541 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7A.

The 74HC7541; 74HCT7541 provides eight non-inverting buffer/line drivers with 3-state outputs and Schmitt-trigger action. The 3-state outputs are controlled by the output enable inputs OE1 and OE2. A HIGH on OEn causes the outputs to assume a high-impedance OFF-state. Schmitt trigger action on the data inputs transforms slowly changing input signals into sharply defined, jitter-free output signals.

The 74HC7541; 74HCT7541 is identical to the 74HC541; 74HCT541 but has hysteresis on the data inputs.

2. **Features and benefits**

- Non-inverting outputs
- Low-power dissipation
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

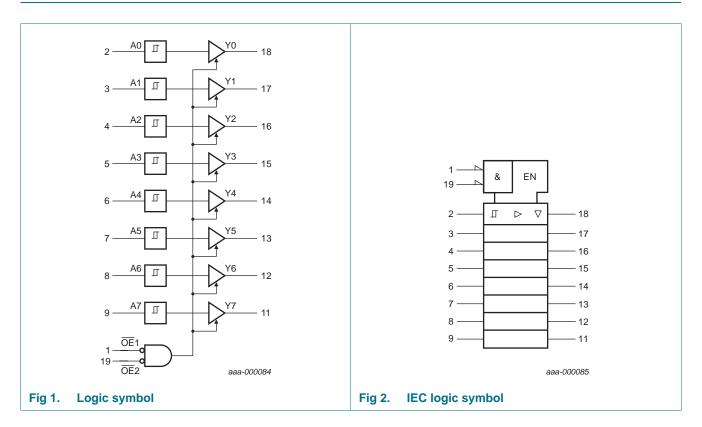
Ordering information 3.

Table 1. **Ordering information**

Type number	Package	Package									
	Temperature range	Name	Description	Version							
74HC7541N	−40 °C to +125 °C	DIP20	plastic dual in-line package; 20 leads (300 mil)	SOT146-1							
74HCT7541N											
74HC7541D	−40 °C to +125 °C	SO20	plastic small outline package; 20 leads;	SOT163-1							
74HCT7541D			body width 7.5 mm								
74HC7541DB	–40 °C to +125 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1							
74HC7541PW	−40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads;	SOT360-1							
74HCT7541PW			body width 4.4 mm								

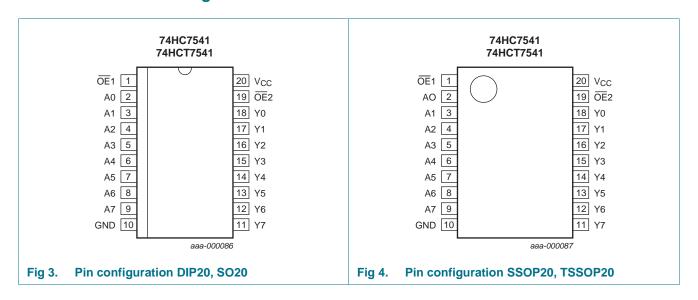


4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
OE1	1	output enable input (active LOW)
A0 to A7	2, 3, 4, 5, 6, 7, 8, 9	data input
GND	10	ground (0 V)
Y0 to Y7	18, 17, 16, 15, 14, 13, 12, 11	data output
OE ₂	19	output enable input (active LOW)
V _{CC}	20	supply voltage

6. Functional description

Table 3. Functional table[1]

Control		Input	Output
OE1	OE2	An	Yn
L	L	L	L
L	L	Н	Н
X	Н	X	Z
Н	X	X	Z

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> -	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> -	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		−65	+150	°C
P _{tot}	total power dissipation		[2]		
	DIP20		-	750	mW
	SO20, SSOP20, TSSOP20		-	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] For DIP20 packages: above 70 °C the value of P_{tot} derates linearly with 12 mW/K.
For SO20 packages: above 70 °C the value of P_{tot} derates linearly with 8 mW/K.
For SSOP20 and TSSOP20 packages: above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.

Recommended operating conditions

Table 5. **Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC75	541		74HCT	Unit		
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C

Static characteristics

Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Ta	_{mb} = 25	5 °C		= −40 °C ⊦85 °C	T _{amb} = −40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC75	41				•	'	1	•		
V_{OH}	HIGH-level	$V_I = V_{T+}$ or V_{T-}								
	output voltage	$I_O = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \ \mu A; \ V_{CC} = 4.5 \ V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20 \mu A$; $V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_O = -6.0$ mA; $V_{CC} = 4.5$ V	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL} LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}									
	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V	
		I_O = 20 μ A; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	0	0.1	-	0.1	-	0.1	V
		I_{O} = 6.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_{O} = 7.8 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
C _I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT7	541									
V _{OH}	HIGH-level	$V_I = V_{T+}$ or V_{T-} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -20 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -6.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	$V_{I} = V_{T+} \text{ or } V_{T-}; V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_O = 20 \mu A;$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 6.0 \text{ mA};$	-	0.15	0.26	-	0.33	-	0.4	V

74HC_HCT7541

All information provided in this document is subject to legal disclaimers.

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +85 °C		T _{amb} = -40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Δl _{CC}	additional supply current	per input pin; $I_O = 0$ A; $V_I = V_{CC} - 2.1$ V; other inputs at V_{CC} or GND; $V_{CC} = 4.5$ V to 5.5 V								
		An input	-	20	72	-	90	-	98	μΑ
		OEn input	-	130	468	-	585	-	637	μΑ
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

 $GND = 0 \ V; \ C_L = 50 \ pF;$ for test circuit see <u>Figure 7</u>.

Symbol	Parameter	Conditions		Tan	_{1b} = 25	°C	$T_{amb} = -40^{\circ}$	°C to +125 °C	Unit
				Min	Тур	Max	Max (85 °C)	Max (125 °C)	
74HC754	11								
t _{pd}	propagation delay	An to Yn; see Figure 5	[1]						
		$V_{CC} = 2.0 \text{ V}$		-	39	120	150	180	ns
		$V_{CC} = 4.5 \text{ V}$		-	14	24	30	36	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	10	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}$		-	11	20	26	32	ns
t _{en} enable time		OEn to Yn; see Figure 6	[1]						
		$V_{CC} = 2.0 \text{ V}$		-	44	160	200	240	ns
		$V_{CC} = 4.5 \text{ V}$		-	16	32	40	48	ns
		$V_{CC} = 6.0 \text{ V}$		-	13	27	34	41	ns
t _{dis}	disable time	OEn to Yn; see Figure 6	[1]						
		$V_{CC} = 2.0 \text{ V}$		-	58	160	200	240	ns
		$V_{CC} = 4.5 \text{ V}$		-	21	32	40	48	ns
		$V_{CC} = 6.0 \text{ V}$		-	17	27	34	41	ns
t _t	transition time	see Figure 5	[2]						
		$V_{CC} = 2.0 \text{ V}$		-	14	60	75	90	ns
		V _{CC} = 4.5 V		-	5	12	15	18	ns
		V _{CC} = 6.0 V		-	4	10	13	15	ns
C_{PD}	power dissipation capacitance	per package; $V_I = GND$ to V_{CC}	[3]	-	30	-	-	-	pF

Table 7. Dynamic characteristics

 $GND = 0 \ V; \ C_L = 50 \ pF;$ for test circuit see <u>Figure 7</u>.

Symbol	Parameter	Conditions		Tan	_{nb} = 25	°C	$T_{amb} = -40^{\circ}$	°C to +125 °C	Unit
				Min	Тур	Max	Max (85 °C)	Max (125 °C)	
74HCT7	541								
t _{pd}	propagation delay	An to Yn; see Figure 5	[1]						
		$V_{CC} = 4.5 \text{ V}$		-	19	32	40	48	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	16	-	-	-	ns
t _{en}	enable time	OEn to Yn; see Figure 6	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}$		-	18	32	40	48	ns
t _{dis}	disable time	OEn to Yn; see Figure 6	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}$		-	20	32	40	48	ns
t _t	transition time	V _{CC} = 4.5 V; see <u>Figure 5</u>	[2]	-	5	12	15	18	ns
C_{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} – 1.5 V	[3]	-	32	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL} .
 - t_{en} is the same as t_{PZL} and t_{PZH} .
 - t_{dis} is the same as t_{PLZ} and $t_{\text{PHZ}}.$
- [2] t_t is the same as t_{THL} and t_{TLH} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

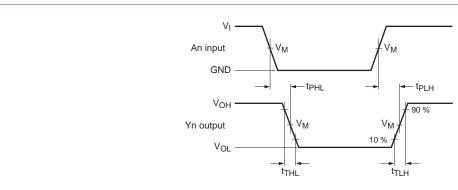
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$

11. Waveforms



aaa-000088

Measurement points are given in Table 8.

 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 5. Input to output propagation delays

74HC_HCT7541

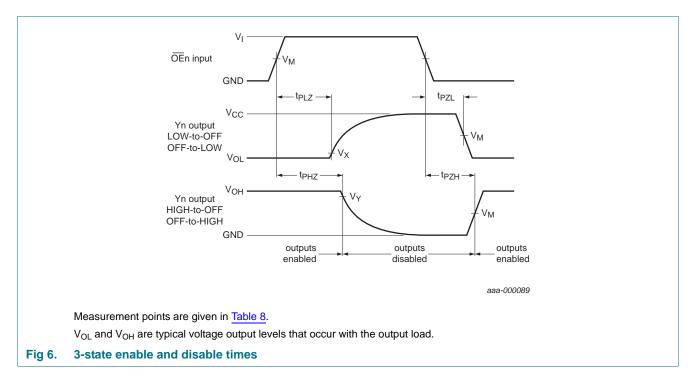
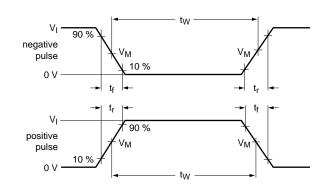
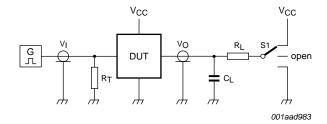


Table 8. Measurement points

Туре	Input	Output							
	V_{M}	V _M	V_X	V _Y					
74HC7541	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}					
74HCT7541	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}					

7 of 17





Test data is given in Table 9.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator

C_L = Load capacitance including jig and probe capacitance

R_L = Load resistance

S1 = Test selection switch

Fig 7. Test circuit for measuring switching times

Table 9. Test data

Туре	Input		Load		S1 position				
	VI	t _r , t _f	C _L R _L		t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}		
74HC7541	V_{CC}	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}		
74HCT7541	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}		

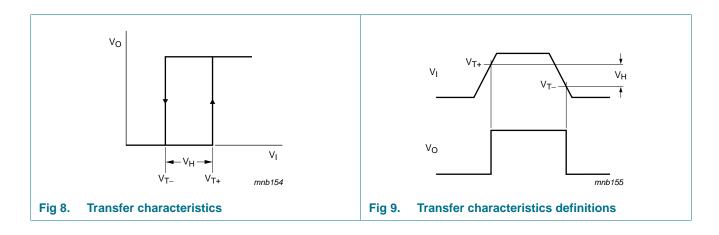
12. Transfer characteristics

Table 10. Transfer characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); see Figure 8 and Figure 9.

Symbol	Parameter	Conditions	Tar	_{nb} = 25	°C	T _{amb} = -40 °C to +85 °C		T _{amb} = -40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC754	41							1		
V_{T+}	positive-going	V _{CC} = 2.0 V	-	-	1.5	-	1.5	-	1.5	V
	threshold	V _{CC} = 4.5 V	-	-	3.15	-	3.15	-	3.15	V
	voltage	V _{CC} = 6.0 V	-	-	4.2	-	4.2	-	4.2	V
V_{T-}		V _{CC} = 2.0 V	0.3	-	-	0.3	-	0.3	-	V
threshold voltage		V _{CC} = 4.5 V	1.35	-	-	1.35	-	1.35	-	V
	voitage	V _{CC} = 6.0 V	1.8	-	-	1.8	-	1.8	-	V
V_{H}	hysteresis	V _{CC} = 2.0 V	0.1	0.20	-	0.1	-	0.1	-	V
	voltage	V _{CC} = 4.5 V	0.25	0.40	-	0.25	-	0.25	-	V
		V _{CC} = 6.0 V	0.3	0.5	-	0.3	-	0.3	-	V
74HCT7	541									
V_{T+}	positive-going	V _{CC} = 4.5 V	-	-	2.0	-	2.0	-	2.0	V
	threshold voltage	V _{CC} = 5.5 V	-	-	2.1	-	2.1	-	2.1	V
V_{T-}	negative-going	V _{CC} = 4.5 V	0.7	-	-	0.64	-	0.6	-	V
	threshold voltage	V _{CC} = 5.5 V	8.0	-	-	0.74	-	0.7	-	V
V_{H}	hysteresis	$V_{CC} = 4.5 \text{ V}$	0.17	0.23	-	-	-	-	-	V
	voltage	V _{CC} = 5.5 V	0.17	0.23	-	-	-	-	-	V

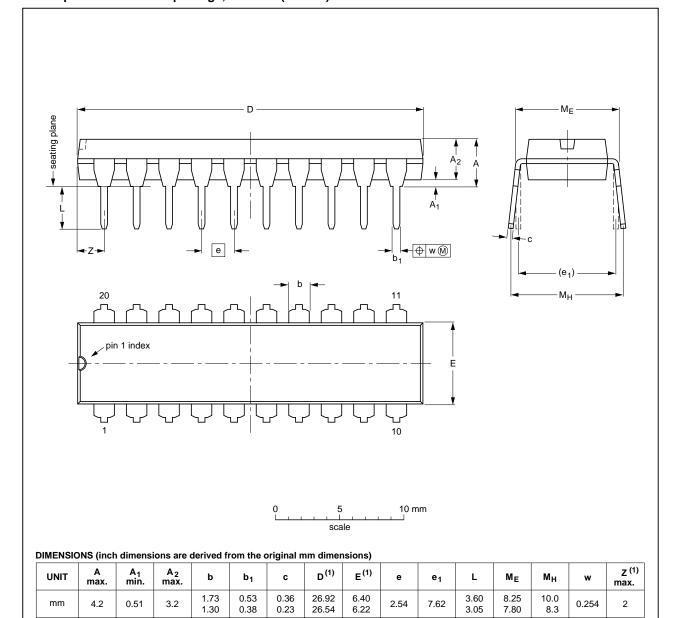
13. Transfer characteristics waveforms



14. Package outline

DIP20: plastic dual in-line package; 20 leads (300 mil)

SOT146-1



. . .

inches

0.17

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

0.068

0.051

0.021

0.014

0.009

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT146-1		MS-001	SC-603		99-12-27 03-02-13	

1.060

1.045

0.25

0.14

0.3

0.32

0.39

Fig 10. Package outline SOT146-1 (DIP20)

0.02

0.13

74HC_HCT7541 All information provided in this document is subject to legal disclaimers.

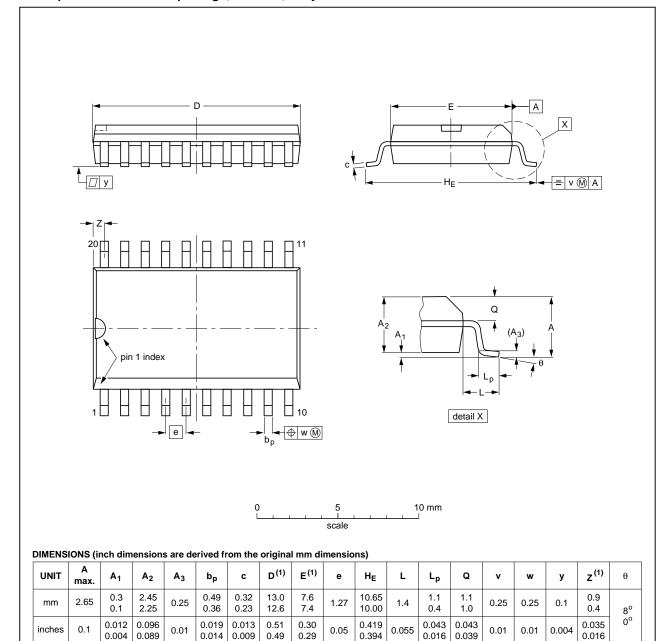
© NXP B.V. 2011. All rights reserved.

0.078

0.01

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

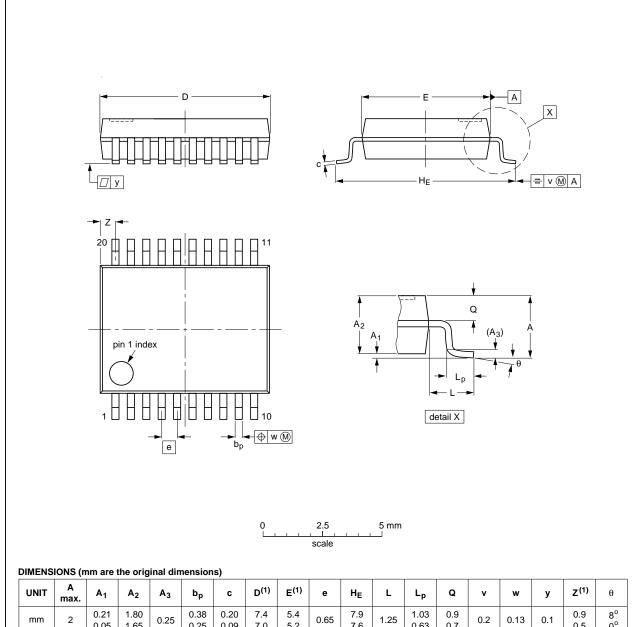
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT163-1	075E04	MS-013			-99-12-27 03-02-19	

Fig 11. Package outline SOT163-1 (SO20)

74HC_HCT7541 All information provided in this document is subject to legal disclaimers.

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1



- 3							-,												
	UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
	mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	7.4 7.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.9 0.5	8° 0°

1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

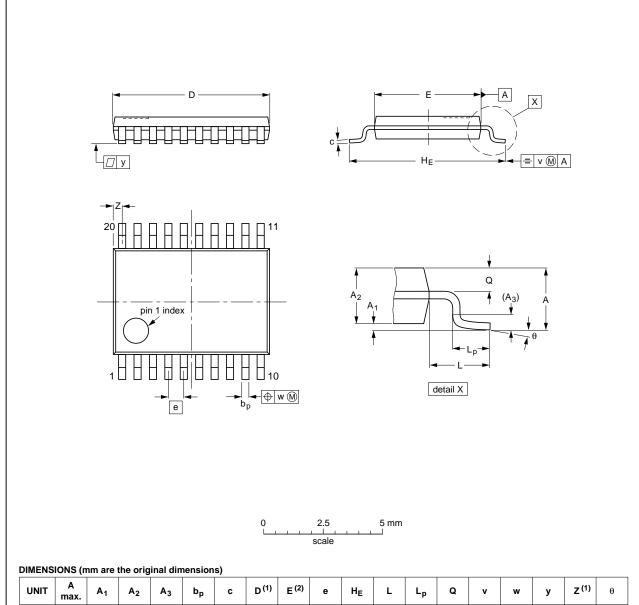
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT339-1		MO-150			99-12-27 03-02-19

Fig 12. Package outline SOT339-1 (SSOP20)

74HC_HCT7541 All information provided in this document is subject to legal disclaimers.

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E (2)	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATE			
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE		
SOT360-1		MO-153			99-12-27 03-02-19		
				1	03-02-19	,	

Fig 13. Package outline SOT360-1 (TSSOP20)

74HC_HCT7541

All information provided in this document is subject to legal disclaimers.

15. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

16. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes				
74HC_HCT7541 v.3	20110725	Product data sheet	-	74HC_HCT7541_CNV v.2				
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 							
	 Legal texts have 	ave been adapted to the new o	company name wher	e appropriate.				
	 Added type n 	numbers 74HC7541PW and 74	HCT7541PW (TSSC	OP20 package).				
74HC_HCT7541_CNV v.2	19970917	Product specification	-	-				

17. Legal information

17.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

17.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

17.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This NXP Semiconductors product has been qualified for use in automotive applications. The product is not designed, authorized or warranted to be

suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

74HC_HCT7541

74HC7541; 74HCT7541

Octal Schmitt trigger buffer/line driver; 3-state

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

17.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

18. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

19. Contents

1	General description
2	Features and benefits
3	Ordering information 1
4	Functional diagram 2
5	Pinning information
5.1	Pinning
5.2	Pin description
6	Functional description 3
7	Limiting values 3
8	Recommended operating conditions 4
9	Static characteristics 4
10	Dynamic characteristics 5
11	Waveforms
12	Transfer characteristics 9
13	Transfer characteristics waveforms 9
14	Package outline 10
15	Abbreviations
16	Revision history
17	Legal information
17.1	Data sheet status
17.2	Definitions
17.3	Disclaimers
17.4	Trademarks16
18	Contact information
40	Contents 47

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.